

358-848

MAXIMUM RATINGS

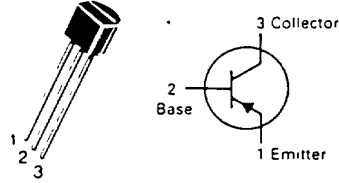
Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CBO}	40	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	200	mA _{dc}
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Power Dissipation @ $T_A = 60^\circ\text{C}$	P_D	250	mW
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	°C

***THERMAL CHARACTERISTICS**

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

**2N3905
2N3906**

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



**GENERAL PURPOSE
TRANSISTOR**

PNP SILICON

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(1) ($I_C = 1.0 \text{ mA}_{dc}, I_B = 0$)	$V_{(BR)CEO}$	40	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10 \mu\text{A}_{dc}, I_E = 0$)	$V_{(BR)CBO}$	40	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10 \mu\text{A}_{dc}, I_C = 0$)	$V_{(BR)EBO}$	5.0	—	Vdc
Base Cutoff Current ($V_{CE} = 30 \text{ Vdc}, V_{BE} = 3.0 \text{ Vdc}$)	I_{BL}	—	50	nA _{dc}
Collector Cutoff Current ($V_{CE} = 30 \text{ Vdc}, V_{BE} = 3.0 \text{ Vdc}$)	I_{CEX}	—	50	nA _{dc}
ON CHARACTERISTICS(1)				
DC Current Gain ($I_C = 0.1 \text{ mA}_{dc}, V_{CE} = 1.0 \text{ Vdc}$)	h_{FE}	30	—	—
		60	—	
		40	—	
		80	—	
		50	150	
		100	300	
		30	—	
		60	—	
		15	—	
		30	—	
Collector-Emitter Saturation Voltage ($I_C = 10 \text{ mA}_{dc}, I_B = 1.0 \text{ mA}_{dc}$) ($I_C = 50 \text{ mA}_{dc}, I_B = 5.0 \text{ mA}_{dc}$)	$V_{CE(sat)}$	—	0.25 0.4	Vdc
Base-Emitter Saturation Voltage ($I_C = 10 \text{ mA}_{dc}, I_B = 1.0 \text{ mA}_{dc}$) ($I_C = 50 \text{ mA}_{dc}, I_B = 5.0 \text{ mA}_{dc}$)	$V_{BE(sat)}$	0.65	0.85 0.95	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 10 \text{ mA}_{dc}, V_{CE} = 20 \text{ Vdc}, f = 100 \text{ MHz}$)	f_T	200 250	—	MHz
Output Capacitance ($V_{CB} = 5.0 \text{ Vdc}, I_E = 0, f = 100 \text{ kHz}$)	C_{obo}	—	4.5	pF

MOTOROLA SMALL-SIGNAL SEMICONDUCTORS

2N3905, 2N3906

ELECTRICAL CHARACTERISTICS (continued) ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Input Capacitance ($V_{BE} = 0.5\text{ Vdc}$, $I_C = 0$, $f = 100\text{ kHz}$)	C_{ibo}	—	10.0	pF
Input Impedance ($I_C = 1.0\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$)	h_{ie}	0.5 2.0	8.0 12	k ohms
Voltage Feedback Ratio ($I_C = 1.0\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$)	h_{re}	0.1 0.1	5.0 10	$\times 10^{-4}$
Small-Signal Current Gain ($I_C = 1.0\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$)	h_{fe}	50 100	200 400	—
Output Admittance ($I_C = 1.0\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$)	h_{oe}	1.0 3.0	40 60	μmhos
Noise Figure ($I_C = 100\ \mu\text{A}$, $V_{CE} = 5.0\text{ Vdc}$, $R_S = 1.0\text{ k ohm}$, $f = 10\text{ Hz to }15.7\text{ kHz}$)	NF	— —	5.0 4.0	dB

SWITCHING CHARACTERISTICS

Delay Time	$(V_{CC} = 3.0\text{ Vdc}$, $V_{BE} = 0.5\text{ Vdc}$ $I_C = 10\text{ mAdc}$, $I_{B1} = 1.0\text{ mAdc}$)	t_d	—	35	ns
Rise Time		t_r	—	35	ns
Storage Time		t_s	—	200 225	ns
Fall Time	$(V_{CC} = 3.0\text{ Vdc}$, $I_C = 10\text{ mAdc}$, $I_{B1} = I_{B2} = 1.0\text{ mAdc}$)	t_f	—	60 75	ns

(1) Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

FIGURE 1 – DELAY AND RISE TIME EQUIVALENT TEST CIRCUIT

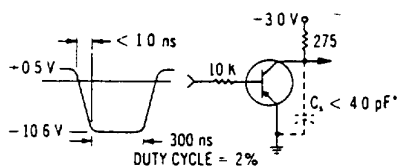
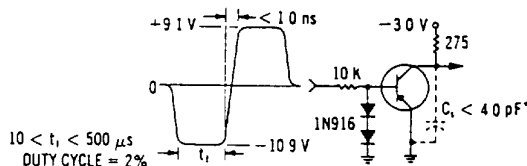


FIGURE 2 – STORAGE AND FALL TIME EQUIVALENT TEST CIRCUIT



*Total shunt capacitance of test jig and connectors

TRANSIENT CHARACTERISTICS

— $T_j = 25^\circ\text{C}$ --- $T_j = 125^\circ\text{C}$

FIGURE 3 – CAPACITANCE

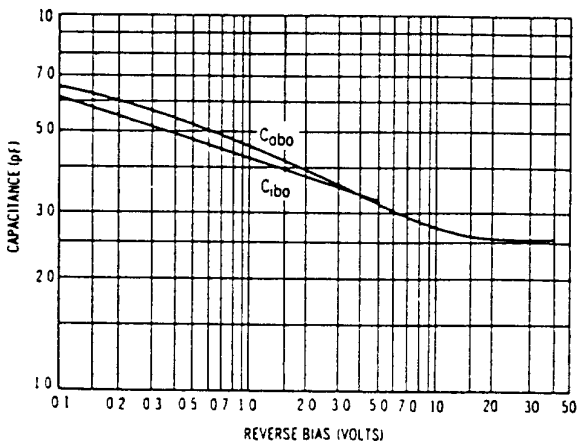
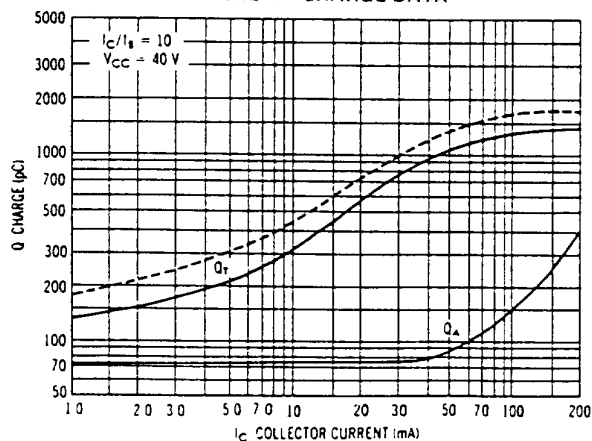


FIGURE 4 – CHARGE DATA



MOTOROLA SMALL-SIGNAL SEMICONDUCTORS

FIGURE 5 - TURN ON TIME

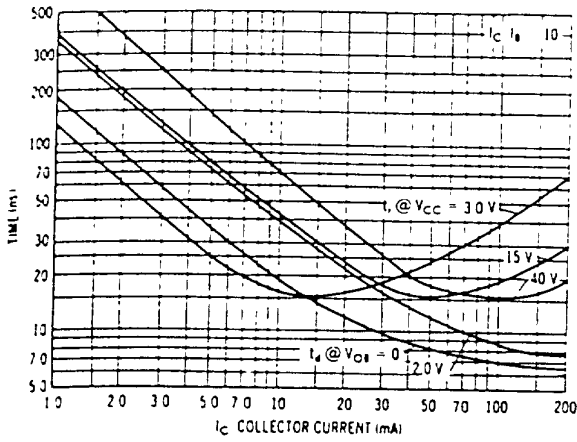
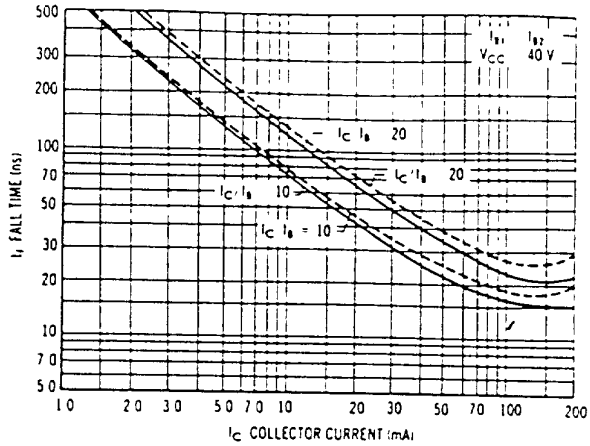


FIGURE 6 - FALL TIME



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AUDIO SMALL SIGNAL CHARACTERISTICS
NOISE FIGURE VARIATIONS

$V_{CE} = 5.0$ Vdc, $T_A = 25^\circ\text{C}$,
Bandwidth = 10 Hz

FIGURE 7 -

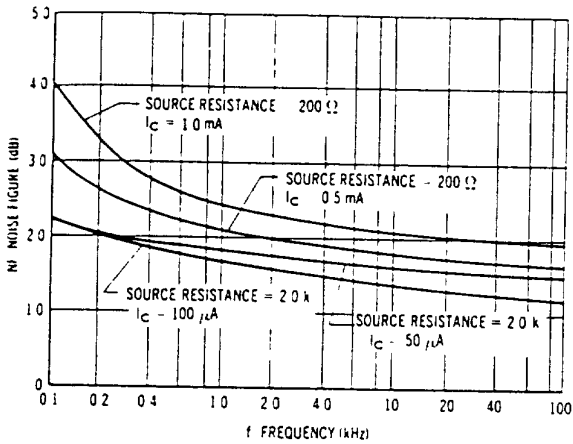
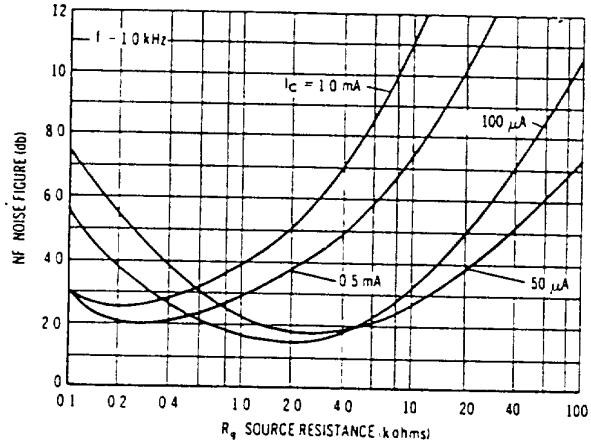


FIGURE 8 -



h PARAMETERS

$(V_{CE} = 10$ Vdc, $f = 1.0$ kHz, $T_A = 25^\circ\text{C})$

FIGURE 9 - CURRENT GAIN

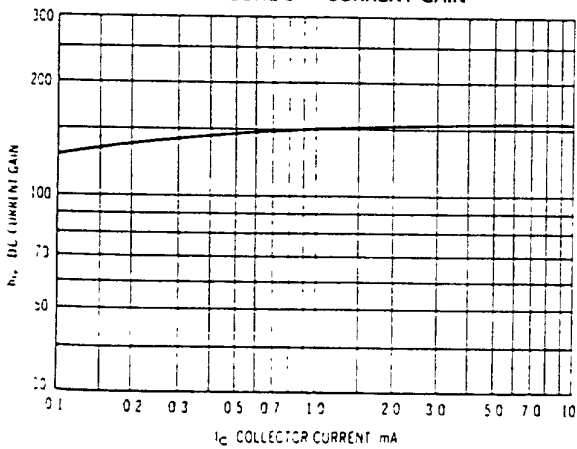
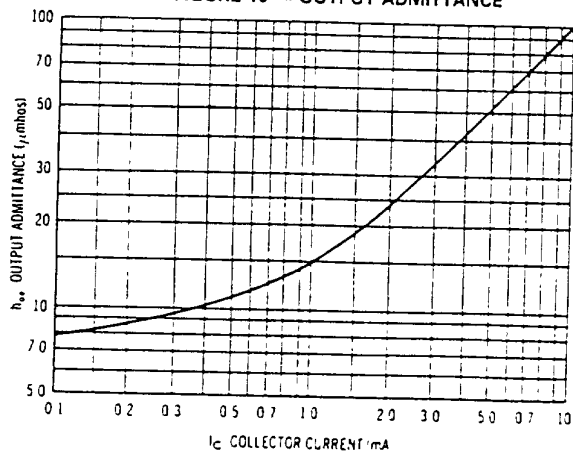


FIGURE 10 - OUTPUT ADMITTANCE



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FIGURE 11 — INPUT IMPEDANCE

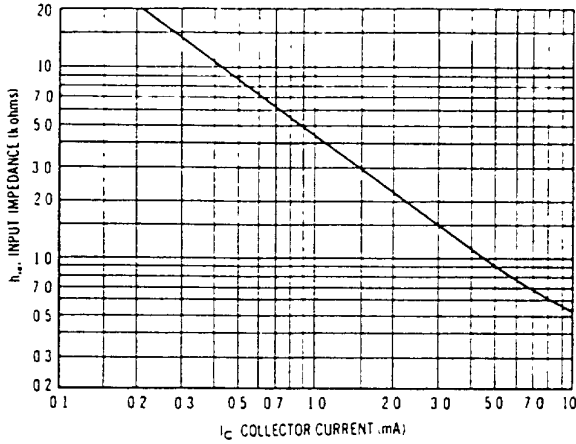
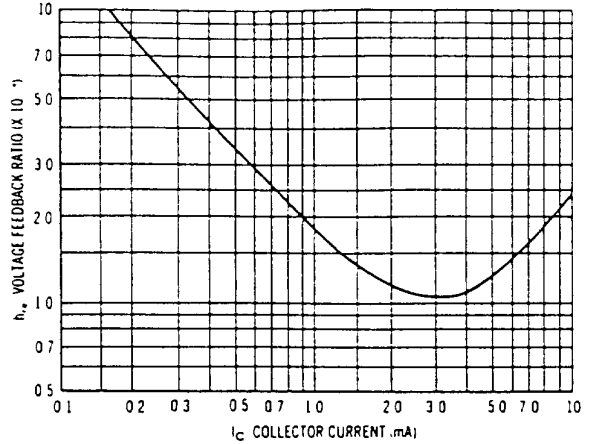


FIGURE 12 — VOLTAGE FEEDBACK RATIO



STATIC CHARACTERISTICS

FIGURE 13 — DC CURRENT GAIN

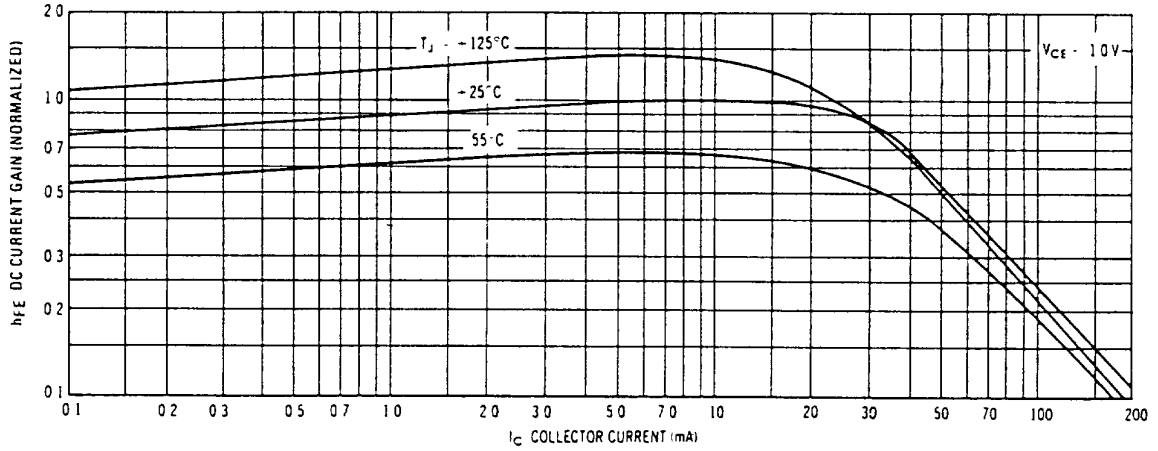
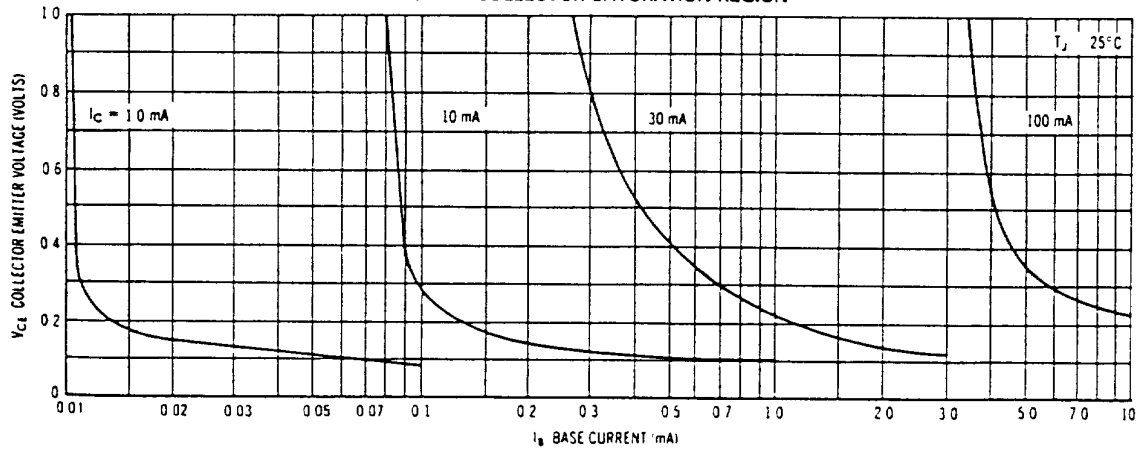
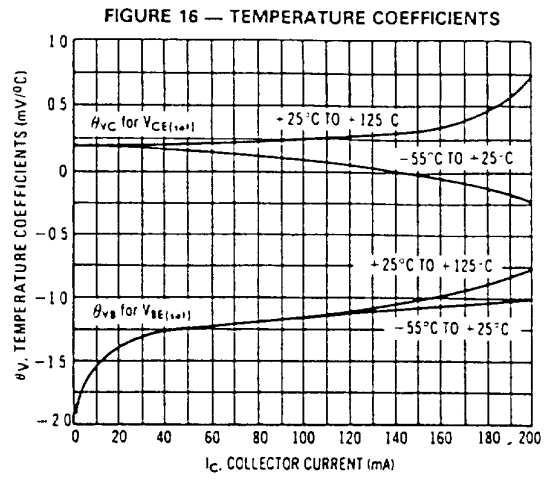
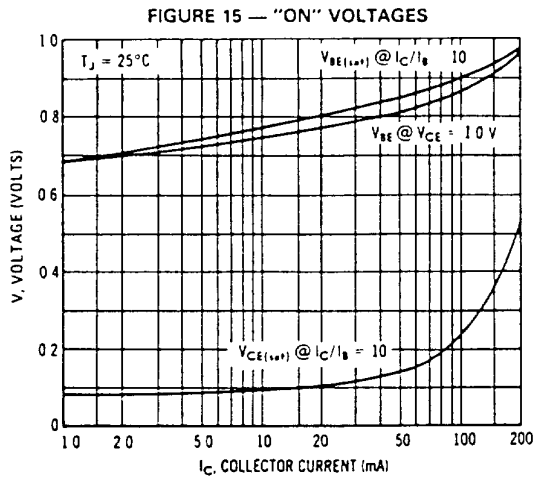


FIGURE 14 — COLLECTOR SATURATION REGION





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